Serial No.

Docket No.: RD-25,993-7

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Barry Lee-Mean Yang et al.

Serial No.:

Filed:

Group Art Unit:

For:

MULTILAYER ARTICLE AND METHOD OF MAKING BY ARC PLASMA DEPOSITION

INFORMATION DISCLOSURE STATEMENT

Honorable Assistant Commissioner of Patents Washington, DC 20231

SIR:

This Information Disclosure Statement is being filed under 37 C.F.R. §1.56 for a Continuation Application, which relies on the filing date of its parent application, such parent application being identified as:

U.S. Patent Application Serial No: 09/271,654

Examiner: M. Padgett

Filed: March 17, 1999

Allowed Date: 11/7/01

Inventor(s):

Barry Lee-Mean Yang et al.

Issue Batch No. O58

MULTILAYER ARTICLE AND METHOD OF MAKING BY ARC PLASMA DEPOSITION Title:

Enclosed are copies of forms PTO-1449 and PTO-892 listing all "prior art" cited and submitted in the parent application. Pursuant to 37 C.F.R. §1.98(d), no actual copies of the documents listed are being furnished to the PTO with this Information Disclosure Statement.

Respectfully submitted,

Robert P. Santandrea

Attorney

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General Electric Company CRD Patent Docket Room 4A59 PO Box 8, Bldg. K-1 Salamone Schenectady, New York 12301

DATE: December 4, 2001

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